General Description

FSMOS® MOSFET is based on Oriental Semiconductor's unique device design to achieve low $R_{DS(ON)}$, low gate charge, fast switching and excellent avalanche characteristics. The low V_{th} series is specially optimized for synchronous rectification systems with low driving voltage.

Features

- Low $R_{DS(ON)}$ & FOM
- Extremely low switching loss
- Excellent reliability and uniformity
- Fast switching and soft recovery

RoHS compliant

Applications

- PD charger
- Motor driver
- Switching voltage regulator
- DC-DC convertor
- Switching mode power supply

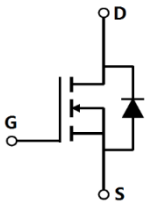
Key Performance Parameters

Parameter	Value	Unit
V_{DS}	100	V
$I_{D,\ pulse}$	304	A
$R_{DS(ON),\ max}$ @ V_{GS}=10V	8.5	mΩ
Q_g	28	nC

Marking Information

Product Name	Package	Marking
SFS10R08PF	TO-220-3L	SFS10R08P

Package & Pin information



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Absolute Maximum Ratings at T_j=25°C unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	100	V
Gate-source voltage	V_{GS}	±20	V
Continuous drain current[1], T_C=25 °C	I_D	76	A
Pulsed drain current[2], T_C=25 °C	$I_{D,\ pulse}$	304	A
Continuous diode forward current[1], T_C=25 °C	I_S	76	A
Diode pulsed current[2], T_C=25 °C	$I_{S,\ pulse}$	304	A
Power dissipation[3], T_C=25 °C	P_D	80	W
Single pulsed avalanche energy[4]	E_{AS}	60	mJ
Operation and storage temperature	T_{stg}, T_j	-55 to 175	°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case	$R_{\theta JC}$	1.8	°C/W
Thermal resistance, junction-ambient	$R_{\theta JA}$	62	°C/W

Electrical Characteristics at T_j=25°C unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	BV_{DSS}	100			V	V_{GS}=0 V, I_D=250 μA
Gate threshold voltage	$V_{GS(th)}$	1		2.5	V	V_{DS}=V_{GS}, I_D=250 μA
Drain-source on-state resistance	$R_{DS(ON)}$		6.8	8.5	mΩ	V_{GS}=10 V, I_D=50A
Drain-source on-state resistance	$R_{DS(ON)}$		9	12	mΩ	V_{GS}=4.5 V, I_D=50A
Gate-source leakage current	I_{GSS}			100	nA	V_{GS}=20 V
				-100		V_{GS}=-20 V
Drain-source leakage current	I_{DSS}			1	μA	V_{DS}=100 V, V_{GS}=0 V
Gate resistance	R_G		2.1		Ω	f=1 MHz, Open drain

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Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	C_{iss}		1890		pF	V_{GS}=0 V, V_{DS}=25 V, f=100 kHz
Output capacitance	C_{oss}		851		pF	
Reverse transfer capacitance	C_{rss}		58		pF	
Turn-on delay time	$t_{d(on)}$		10		ns	V_{GS}=10 V, V_{DS}=50V, R_G=2 Ω, I_D=25 A
Rise time	t_r		13		ns	
Turn-off delay time	$t_{d(off)}$		27		ns	
Fall time	t_f		5		ns	

Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	Q_g		28		nC	V_{GS}=10 V, V_{DS}=50 V, I_D=25 A
Gate-source charge	Q_{gs}		5		nC	
Gate-drain charge	Q_{gd}		5		nC	
Gate plateau voltage	$V_{plateau}$		3.1		V	

Body Diode Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward voltage	V_{SD}			1.3	V	I_S=50 A, V_{GS}=0 V
Reverse recovery time	t_{rr}		55		ns	V_R=50 V, I_S=25 A, di/dt=100 A/μs
Reverse recovery charge	Q_{rr}		64		nC	
Peak reverse recovery current	I_{rrm}		2.2		A	

Note

1) Calculated continuous current based on maximum allowable junction temperature.
2) Repetitive rating; pulse width limited by max. junction temperature.
3) Pd is based on max. junction temperature, using junction-case thermal resistance.
4) V_{DD}=50 V,V_{GS}=10 V, L=0.3 mH, starting T_j=25 °C.

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Electrical Characteristics Diagrams

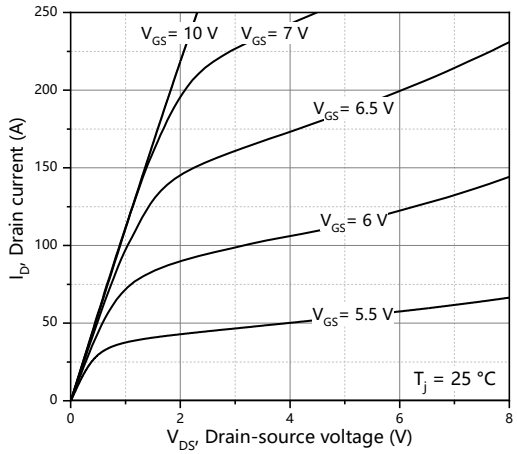

Figure 1. Typ. output characteristics

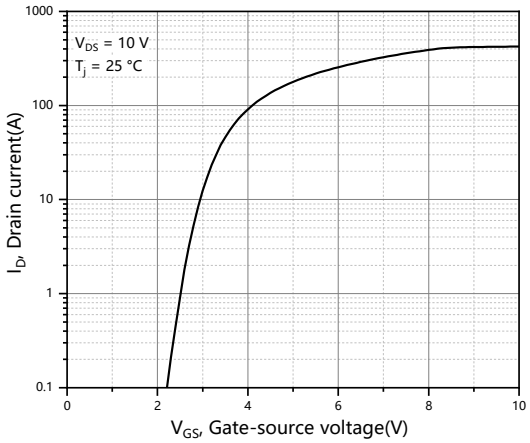

Figure 2. Typ. transfer characteristics

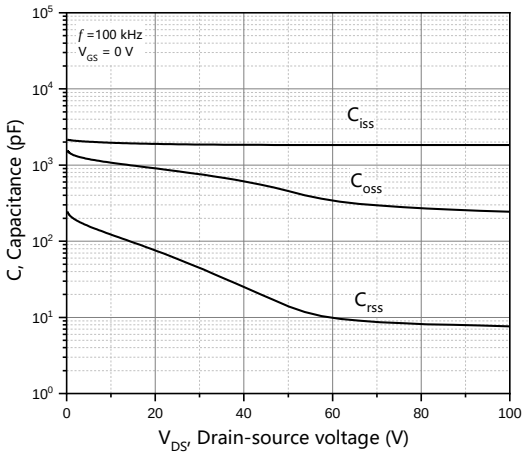

Figure 3. Typ. capacitances

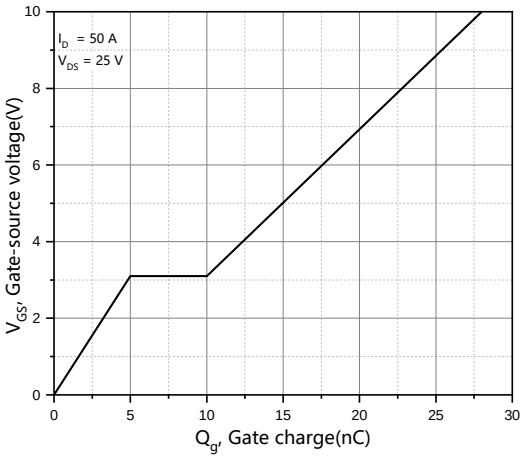

Figure 4. Typ. gate charge

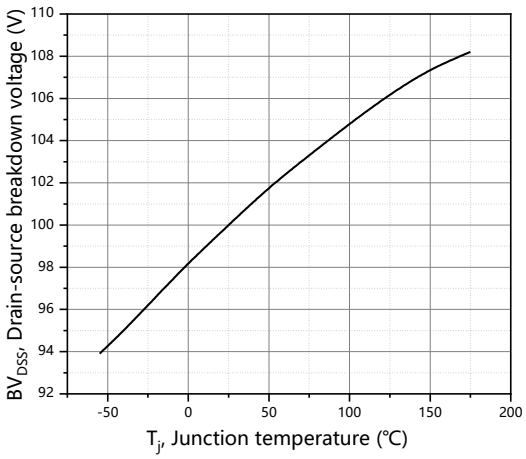

Figure 5. Drain-source breakdown voltage

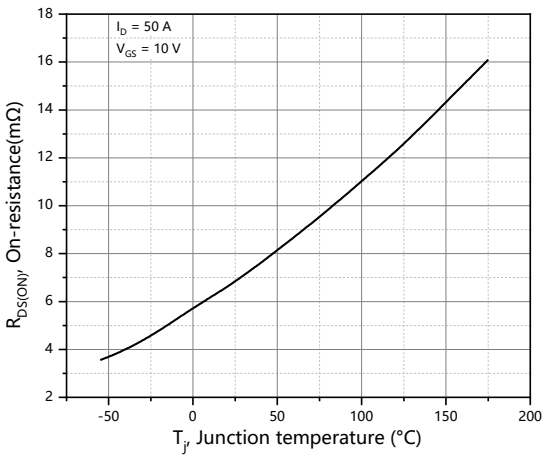

Figure 6. Drain-source on-state resistance

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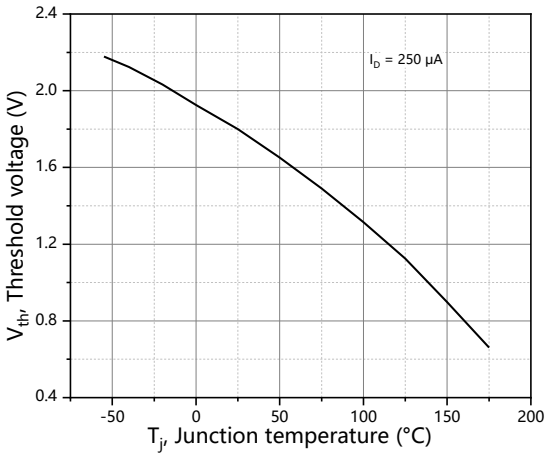

Figure 7. Threshold voltage

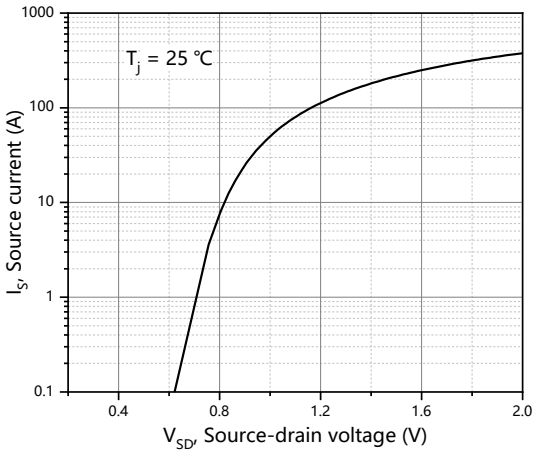

Figure 8. Forward characteristic of body diode

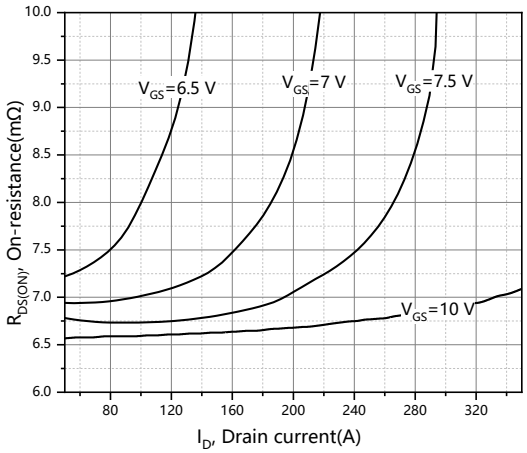

Figure 9. Drain-source on-state resistance

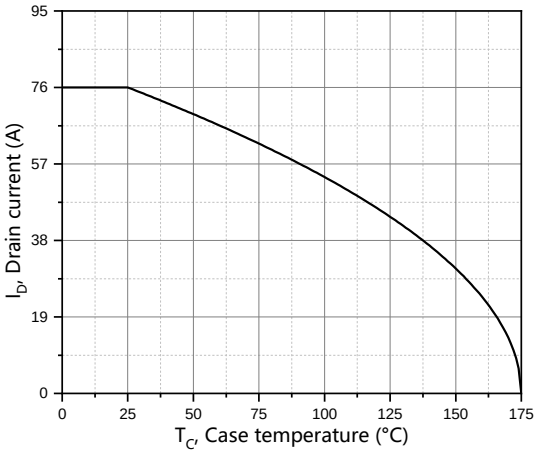

Figure 10. Drain current

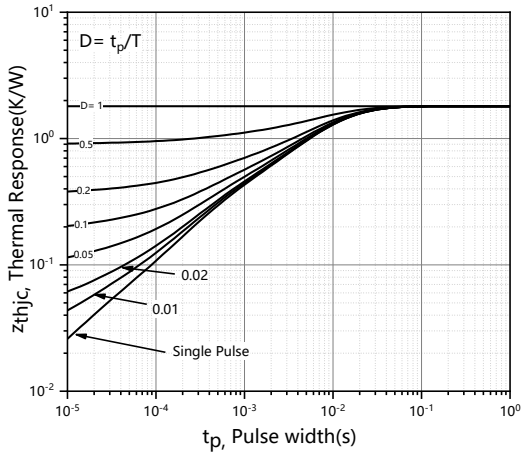

Figure 11. Safe operation area T_C=25℃

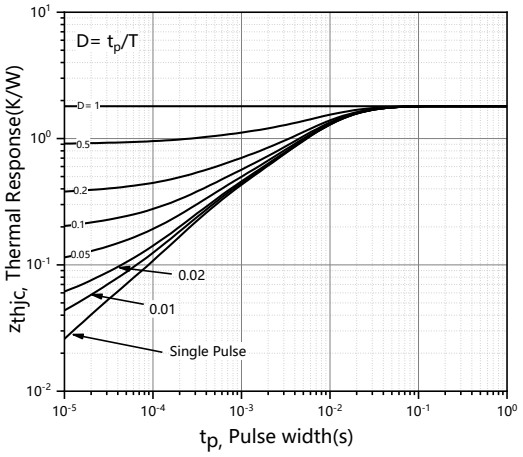

Figure 12. Max. transient thermal impedance

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Test circuits and waveforms

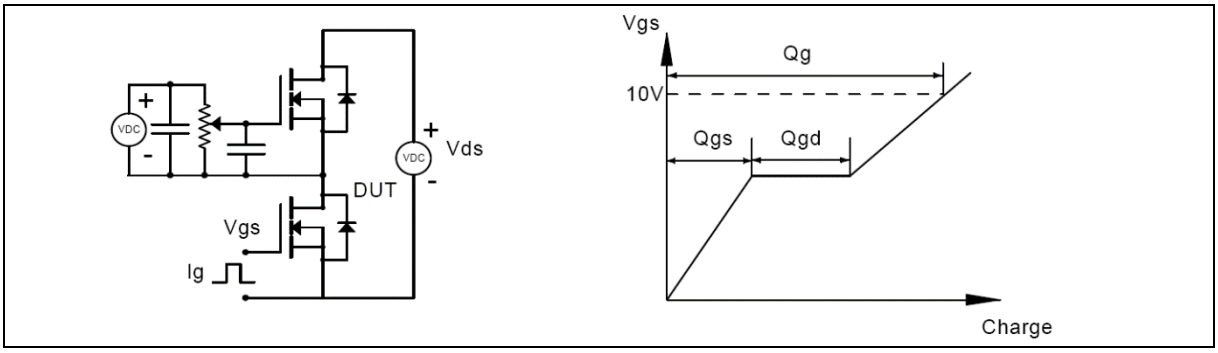

Figure 1. Gate charge test circuit & waveform

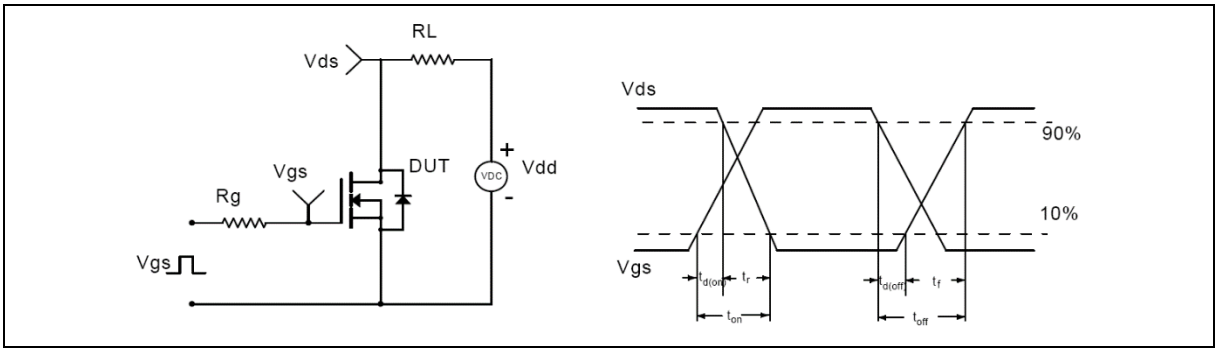

Figure 2. Switching time test circuit & waveforms

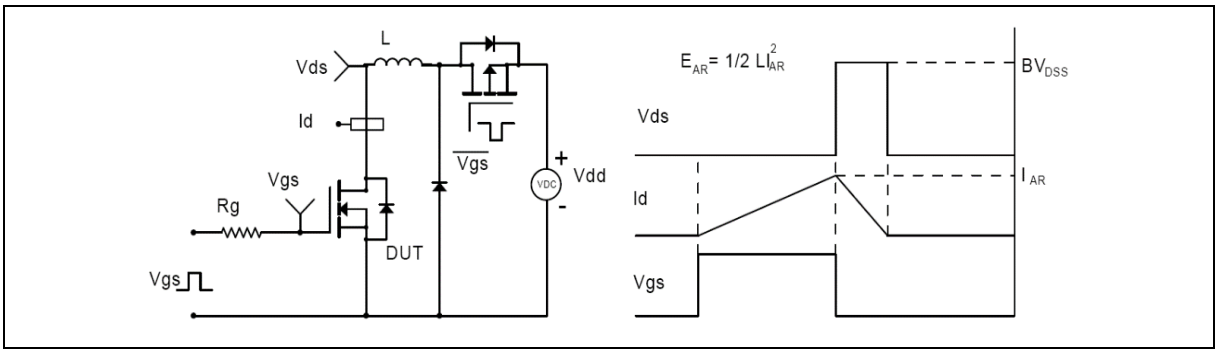

Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms

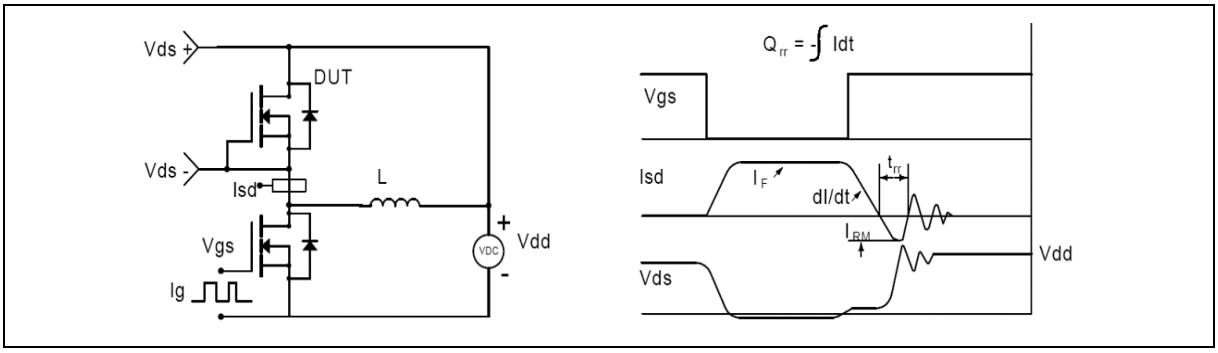

Figure 4. Diode reverse recovery test circuit & waveforms

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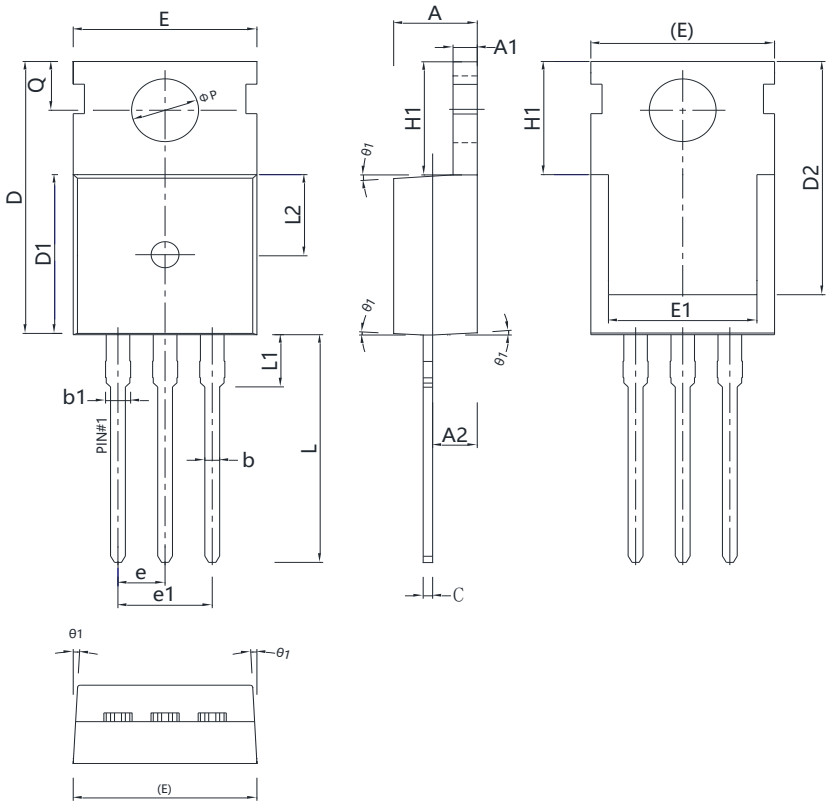

Symbol	mm		
	Min	Nom	Max
A	4.40	4.50	4.60
A1	1.27	1.30	1.33
A2	2.30	2.40	2.50
b	0.70	-	0.90
b1	1.27	-	1.40
c	0.45	0.50	0.60
D	15.30	15.70	16.10
D1	9.10	9.20	9.30
D2	13.10	-	13.70
E	9.70	9.90	10.20
E1	7.80	8.00	8.20
e	2.54 BSC		
e1	5.08 BSC		
H1	6.30	6.50	6.70
L	12.78	13.08	13.38
L1	-	-	3.50
L2	4.60 REF		
ΦP	3.55	3.60	3.65
Q	2.73	-	2.87
θ1	1°	3°	5°

Version : TO-220-3L -J package outline dimension

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Ordering Information

Package Type	Units/ Tube	Tubes/ Inner Box	Units/ Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
TO-220-3L-J	50	20	1000	5	5000

Product Information

Product	Package	Pb Free	RoHS	Halogen Free
SFS10R08PF	TO-220-3L	yes	yes	yes

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Revision History

Version	Revision History	Date
V1.0	Initial release	2023-10-12

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